

METHOD AND APPARATUS FOR REDUCING
LEAKAGE CURRENT IN AN SRAM ARRAY

5 ABSTRACT OF THE DISCLOSURE

10 A memory array including a bit cell row, a strap
cell row, a first power supply line, and a first offset
supply line is provided. The bit cell row may include a
bit cell that includes a first transistor disposed in a
first bit cell body region. The first transistor may
15 include a first active region. The strap cell row may
include a strap cell that includes a first strap cell
body region. The first strap cell body region may be
conductively coupled to the first bit cell body region.
The first power supply line may be electrically coupled
20 to the first active region and may provide a first supply
voltage potential to the first active region. The first
offset supply line may be electrically coupled to the
first strap cell body region and may provide a first
offset voltage potential to the first bit cell body
region via the first strap cell body region. The first
supply voltage potential is operable to be different from
the first offset voltage potential.